PNP/NPN Epitaxial Planar Silicon Transistors



2SB1142/2SD1682

50V/2.5A High-Speed Switching Applications

Applications

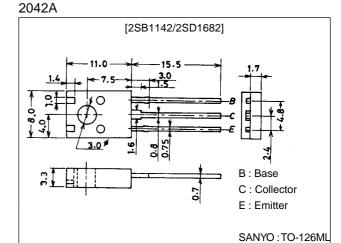
· Power supplies, relay drivers, lamp drivers.

Features

- · Adoption of FBET, MBIT processes.
- · Low saturation voltage.
- · Large current capacity and wide ASO.

Package Dimensions

unit:mm



():2SB1142

Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|------------|-------------|------|
| Collector-to-Base Voltage | V _{CBO} | | (–)60 | V |
| Collector-to-Emitter Voltage | VCEO | | (–)50 | V |
| Emitter-to-Base Voltage | VEBO | | (–)6 | V |
| Collector Current | ۱C | | (–)2.5 | A |
| Collector Current (Pulse) | I _{CP} | | (–)5.0 | A |
| Collector Dissipation | PC | | 1.5 | W |
| | | Tc=25°C | 10 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | | Ratings | | | Unit |
|---|-------------------|---|---------|---------|-----|--------|-------|
| Falameter | | | | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | CB=(-)50V, IE=0 | | | | (–)100 | nA |
| Emitter Cutoff Current | IEBO | EB=(-)4V, IC=0 | | | | (–)100 | nA |
| DC Current Gain | h _{FE} 1 | ⁷ CE=(-)2V, I _C =(-)100mA | | (100)* | | (400)* | |
| | | | | 100* | | 560 | |
| | h _{FE} 2 | CE=(-)2V, IC=(-)2A | | 35 | | | |
| Gain-Bandwidth Product | fT | CE=(-)10V, IC=(-)50mA | | | 140 | | MHz |
| * : The 2SB1142/2SD1682 are classified by 100mA h_{FE} as follows : 2SB1142 100 R 200 140 S 280 200 T 400 | | | | 400 | • | | |
| | | 2SD1682 100 R 200 140 |) S 280 | 200 T | 400 | 280 L | J 560 |

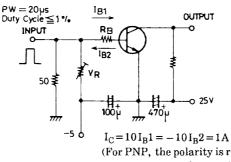
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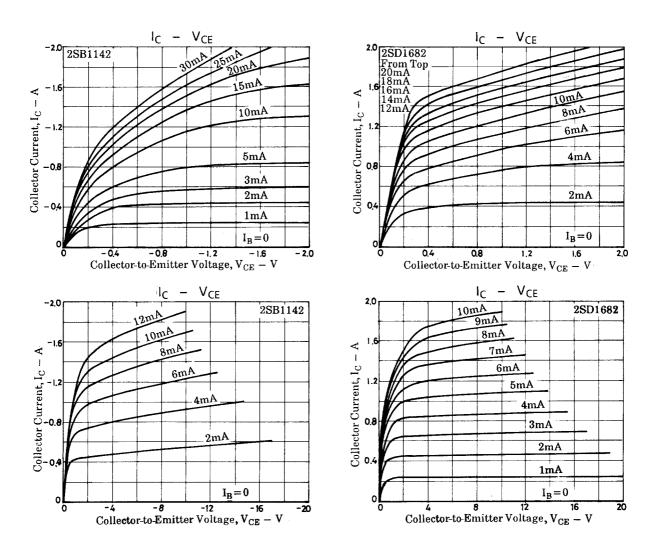
2SB1142/2SD1682

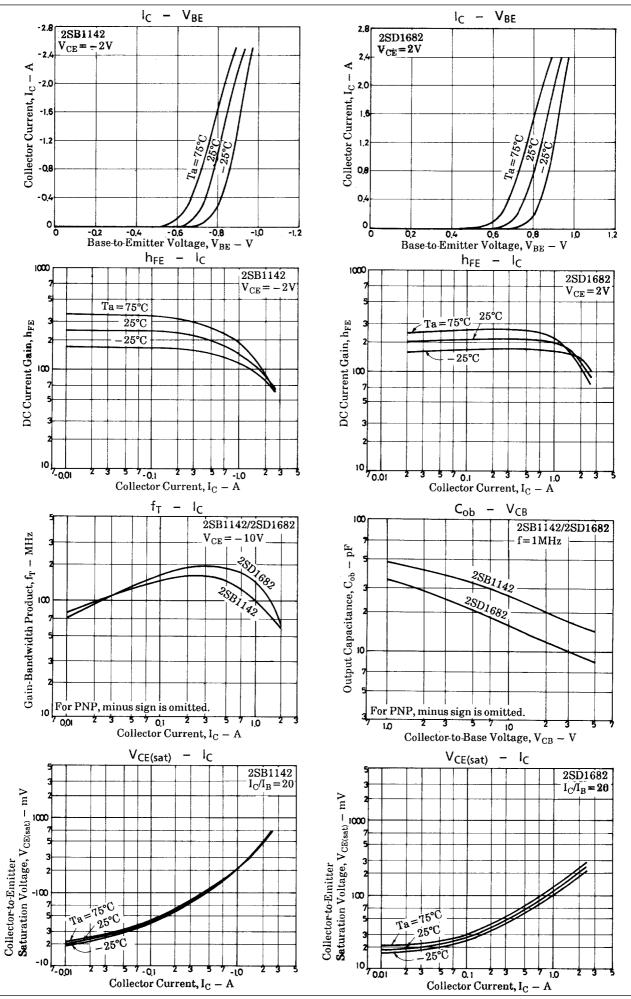
| Parameter | Symbol | Conditions | | Ratings | | |
|---|-----------------------|--|-------|---------|--------|------|
| | | | min | typ | max | Unit |
| Collector-to-Emitter Saturation Voltage | V _{CE(sat)} | I _C =(-)1A, I _B =(-)50mA | | (-250) | (500) | mV |
| | | | | 110 | 300 | mV |
| Base-to-Emitter Saturation Voltage | V _{BE(sat)} | I _C =(-)1A, I _B =(-)50mA | | (–)0.85 | (–)1.2 | V |
| Output Capacitance | C _{ob} | V _{CB} =(-)10V, f=1MHz | | (25)16 | | pF |
| Collector-to-Base Breakdown Voltage | V _(BR) CBO | I _C =(-)10µA, I _E =0 | (–)60 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | I _C =(−)1mA, R _{BE} =∞ | (–)50 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | I _E =(-)10μA, I _C =0 | (–)6 | | | V |
| Turn-ON Time | ton | See specified Test Circuit | | (35)35 | | ns |
| Storage Time | t _{stg} | See specified Test Circuit | | (350) | | ns |
| | | | | 550 | | ns |
| Fall Time | t _f | See specified Test Circuit | | (30)30 | | ns |

Switching Time Test Circuit

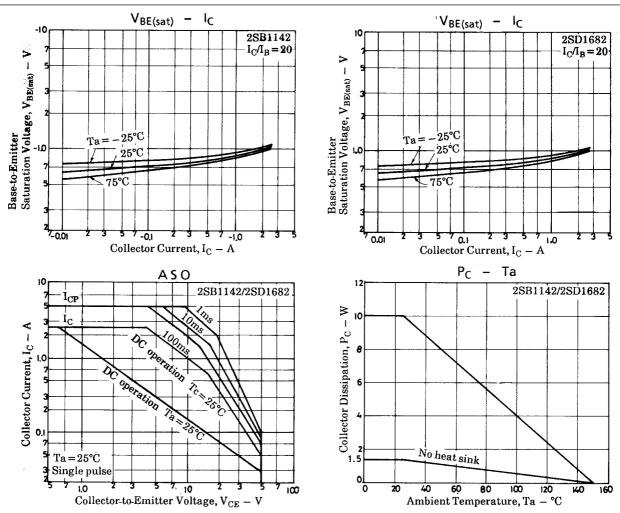


(For PNP, the polarity is reversed). Unit (resistance : Ω , capacitance : F)





2SB1142/2SD1682



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